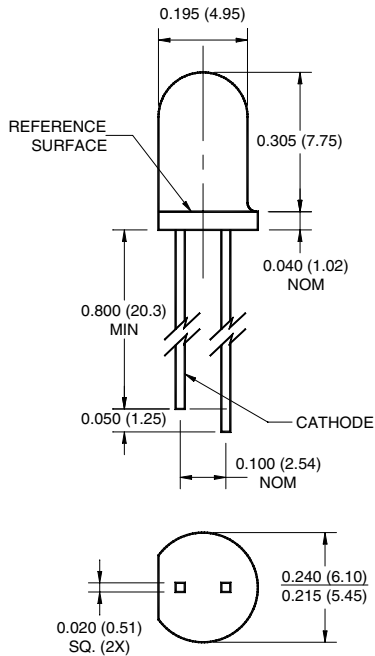


PACKAGE DIMENSIONS

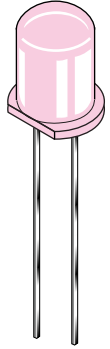


NOTES:

1. Dimensions for all drawings are in inches (mm).
2. Tolerance of $\pm .010$ (.25) on all non-nominal dimensions unless otherwise specified.

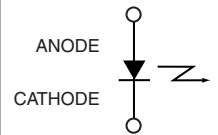
FEATURES

- $\lambda = 880$ nm
- Chip material = AlGaAs
- Package type: T-1 3/4 (5mm lens diameter)
- Matched Photosensor: QSD122/123/124
- Narrow Emission Angle, 18°
- High Output Power
- Package material and color: Clear, peach tinted, plastic



1. Derate power dissipation linearly 2.67 mW/°C above 25°C.
2. RMA flux is recommended.
3. Methanol or isopropyl alcohols are recommended as cleaning agents.
4. Soldering iron 1/16" (1.6mm) minimum from housing.

SCHEMATIC



ABSOLUTE MAXIMUM RATINGS ($T_A = 25^\circ\text{C}$ unless otherwise specified)

| Parameter | Symbol | Rating | Unit |
|---|-------------|----------------|------|
| Operating Temperature | T_{OPR} | -40 to +100 | °C |
| Storage Temperature | T_{STG} | -40 to +100 | °C |
| Soldering Temperature (Iron) ^(2,3,4) | T_{SOL-I} | 240 for 5 sec | °C |
| Soldering Temperature (Flow) ^(2,3) | T_{SOL-F} | 260 for 10 sec | °C |
| Continuous Forward Current | I_F | 100 | mA |
| Reverse Voltage | V_R | 5 | V |
| Power Dissipation ⁽¹⁾ | P_D | 200 | mW |

ELECTRICAL / OPTICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$)

| PARAMETER | TEST CONDITIONS | SYMBOL | MIN | TYP | MAX | UNITS |
|--------------------------|-------------------------------|----------------|-----|---------|-----|---------------|
| Peak Emission Wavelength | $I_F = 20$ mA | λ_{PE} | — | 880 | — | nm |
| Emission Angle | $I_F = 100$ mA | Θ | — | ± 9 | — | Deg. |
| Forward Voltage | $I_F = 100$ mA, $t_p = 20$ ms | V_F | — | — | 1.7 | V |
| Reverse Current | $V_R = 5$ V | I_R | — | — | 10 | μA |
| Radiant Intensity QED121 | $I_F = 100$ mA, $t_p = 20$ ms | I_E | 16 | — | 40 | mW/sr |
| Radiant Intensity QED122 | $I_F = 100$ mA, $t_p = 20$ ms | I_E | 32 | — | 100 | mW/sr |
| Radiant Intensity QED123 | $I_F = 100$ mA, $t_p = 20$ ms | I_E | 50 | — | — | mW/sr |
| Rise Time | $I_F = 100$ mA | t_r | — | 800 | — | ns |
| Fall Time | | t_f | — | 800 | — | ns |

TYPICAL PERFORMANCE CURVES

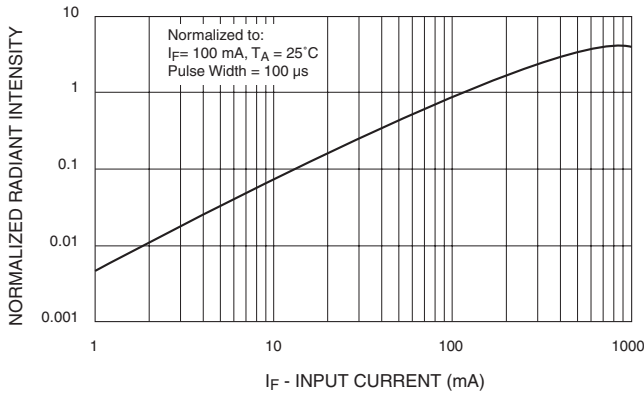


Fig. 1 Normalized Radiant Intensity vs. Input Current

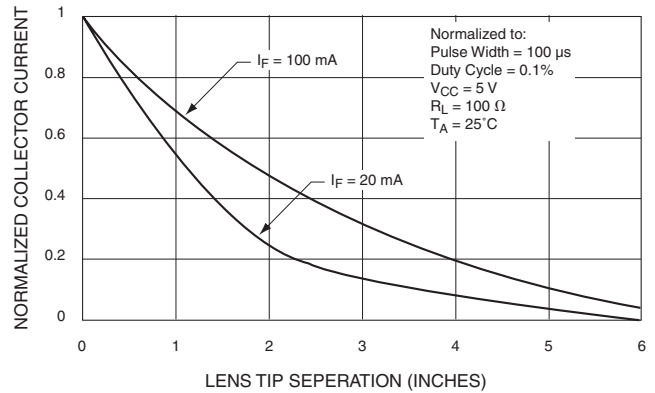


Fig. 2 Coupling Characteristics of QED12X and QSD12X

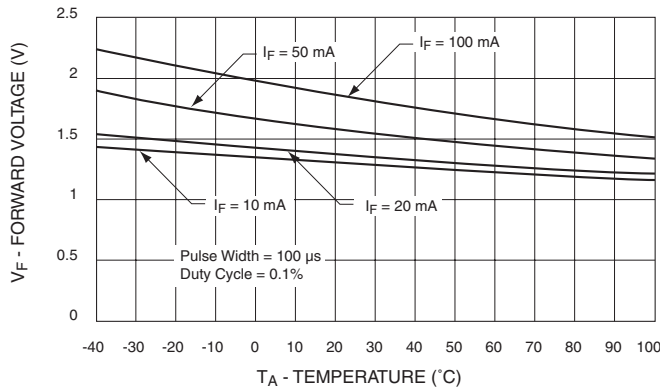


Fig. 3 Forward Voltage vs. Temperature

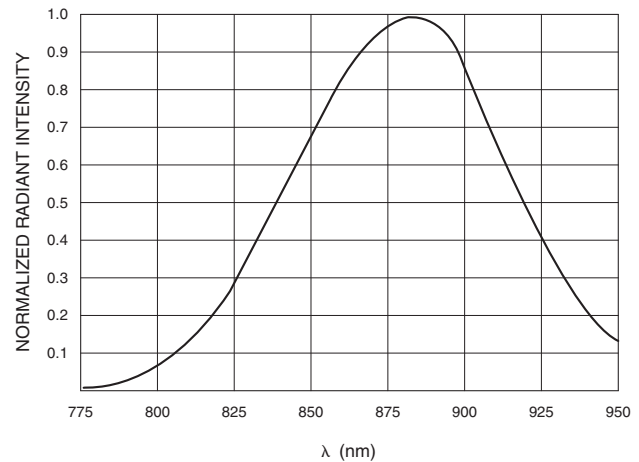


Fig. 4 Normalized Radiant Intensity vs. Wavelength

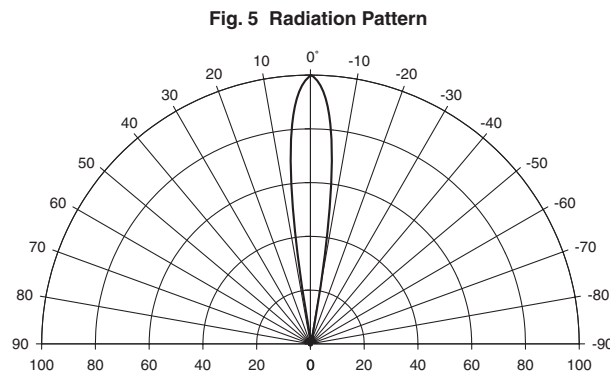


Fig. 5 Radiation Pattern

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